



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D Max T _A = +25°C |
|-------------------|---------------------------------------|--|
| -20V | $75m\Omega$ @ V _{GS} = -4.5V | -3.2A |
| -20V | $110m\Omega$ @ $V_{GS} = -2.5V$ | -2.9A |

Features

- PCB Footprint of 4mm²
- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Maximum Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP2110UFDBQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

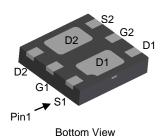
This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power-management applications.

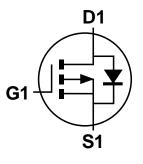
- Load switches
- Power-management functions
- Portable power adaptors

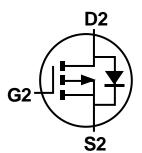
Mechanical Data

- Package: U-DFN2020-6
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Lead-Frame.
 Solderable per MIL-STD-202, Method 208 (4)
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

U-DFN2020-6 (Type B)







Internal Schematic

Ordering Information (Note 4)

| Part Number | Package | Packing | | | |
|-----------------|----------------------|---------|-------------|--|--|
| Part Number | Fackage | Qty. | Carrier | | |
| DMP2110UFDBQ-7 | U-DFN2020-6 (Type B) | 3,000 | Tape & Reel | | |
| DMP2110UFDBQ-13 | U-DFN2020-6 (Type B) | 10,000 | Tape & Reel | | |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

U-DFN2020-6 (Type B)

H6 YWX H6 = Product Type Marking Code
YWX = Date Code Marking
Y = Year (ex: 3 = 2023)
W = Week (ex: a = Week 27; z Represents Week 52 and 53)
X = Internal Code (ex: U = Monday)

Date Code Key

| Year | 2020 | - | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 | 2031 | 2032 |
|------|------|---|------|------|------|------|------|------|------|------|------|------|
| Code | 0 | - | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | 1 | 2 |

| ſ | Week | 1-26 | 27-52 | 53 |
|---|------|------|-------|----|
| | Code | A-Z | a-z | Z |

| Internal Code | Sun | Mon | Tue | Wed | Thu | Fri | Sat |
|---------------|-----|-----|-----|-----|-----|-----|-----|
| Code | Т | U | V | W | Χ | Υ | Z |



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|------------------|----------------------------------|------|--------------|---|
| Drain-Source Voltage | V _{DSS} | -20 | V | | |
| Gate-Source Voltage | Vgss | ±12 | V | | |
| Continuous Drain Current (Note 6) V _{GS} = -4.5V | Steady State | $T_A = +25$ °C $T_A = +70$ °C | ID | -3.2 -2.6 | А |
| Maximum Continuous Body Diode Forward Current (| Is | -1.05 | А | | |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | I _{DM} | -15 | Α | | |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit | |
|--|------------------------|------------------|------|------|
| Total Power Dissipation (Note 5) | T _A = +25°C | PD | 0.82 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | R _{OJA} | 153 | °C/W |
| Total Power Dissipation (Note 6) | T _A = +25°C | PD | 1.14 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | Rөja | 110 | °C/W |
| Operating and Storage Temperature Range | TJ, TSTG | -55 to +150 | °C | |

Electrical Characteristics (@ TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|--|---------------------|-------|------|------|------|---|
| OFF CHARACTERISTICS (Note 7) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -20 | _ | _ | V | $V_{GS} = 0V, I_{D} = -250\mu A$ |
| Zero Gate Voltage Drain Current T _J = +25°C | I _{DSS} | _ | _ | -1.0 | μA | $V_{DS} = -16V, V_{GS} = 0V$ |
| Gate-Source Leakage | Igss | _ | _ | ±100 | nA | $V_{GS} = \pm 8V$, $V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 7) | | | | | • | |
| Gate Threshold Voltage | V _{GS(TH)} | -0.45 | _ | -1.0 | V | $V_{DS} = V_{GS}$, $I_D = -250\mu A$ |
| | | _ | _ | 75 | | Vgs = -4.5V, ID = -2.8A |
| Static Drain-Source On-Resistance | RDS(ON) | _ | _ | 110 | mΩ | V _{GS} = -2.5V, I _D = -2.0A |
| | | _ | _ | 168 | | Vgs = -1.8V, ID = -1.0A |
| Diode Forward Voltage | VsD | _ | _ | -1.0 | V | Vgs = 0V, Is = -1.0A |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | • | |
| Input Capacitance | Ciss | _ | 443 | _ | pF | |
| Output Capacitance | Coss | _ | 59 | _ | pF | V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz |
| Reverse Transfer Capacitance | C _{rss} | _ | 47 | _ | pF | 1 = 1.0IVII 12 |
| Total Gate Charge (V _{GS} = -4.5V) | 0 | _ | 6.0 | _ | nC | |
| Total Gate Charge (V _{GS} = -8V) | Qg | _ | 12.7 | _ | nC | 1, 45,4 0.00 |
| Gate-Source Charge | Q _{gs} | _ | 0.6 | _ | nC | $V_{DS} = -4.5V, I_{D} = -3.0A$ |
| Gate-Drain Charge | Qgd | _ | 1.8 | _ | nC | |
| Turn-On Delay Time | td(ON) | _ | 4.0 | | ns | |
| Turn-On Rise Time | t _R | _ | 3.7 | | ns | V _{DS} = -10V, V _{GS} = -4.5V, |
| Turn-Off Delay Time | tD(OFF) | _ | 24.5 | _ | ns | $R_L = 10\Omega$, $R_g = 6\Omega$ |
| ırn-Off Fall Time t _F | | _ | 9.5 | _ | ns | |
| Body Diode Reverse Recovery Time | trr | _ | 8.3 | _ | ns | Is = -1.0A, dI/dt = 100A/µs |
| Body Diode Reverse Recovery Charge | Q _{RR} | | 2.0 | | nC | Is = -1.0A, dI/dt = 100A/µs |

Notes: 5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.

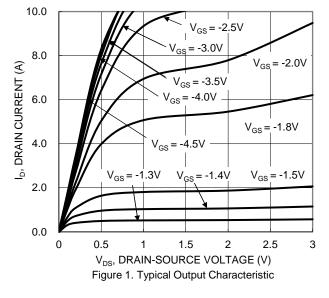
^{6.} Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.

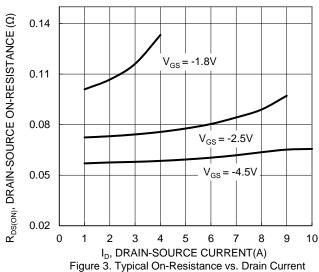
^{7.} Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.









and Gate Voltage

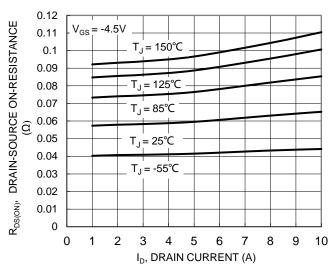
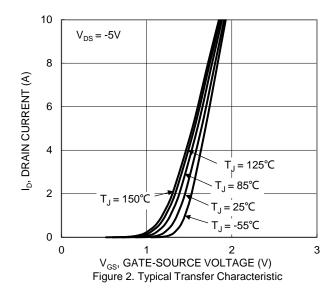
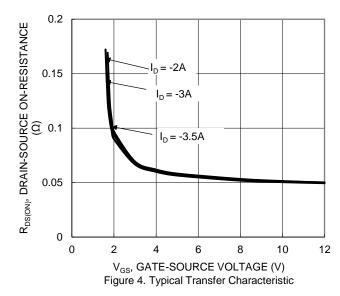


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





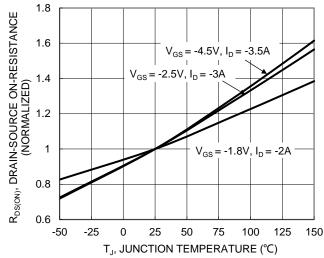


Figure 6. On-Resistance Variation with Junction Temperature





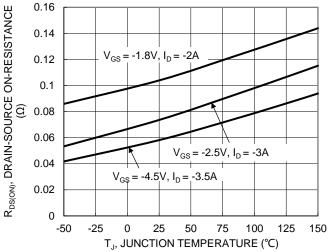
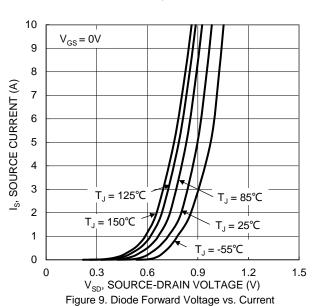


Figure 7. On-Resistance Variation with Junction Temperature



10 8 $V_{GS}(V)$ $V_{DS} = -15V, I_{D} = -6A$ 4 2 0 0 2 4 8 10 12 14 16 18 Qg (nC)

Figure 11. Gate Charge

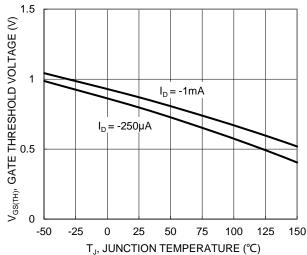
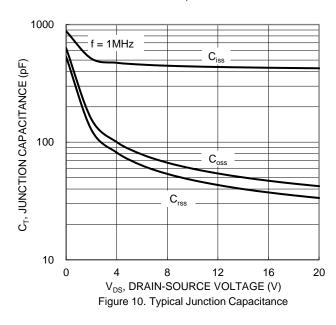
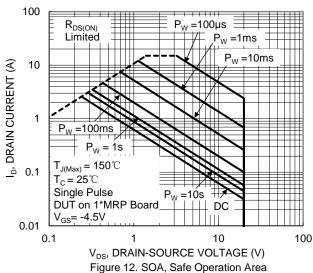


Figure 8. Gate Threshold Variation vs. Junction
Temperature







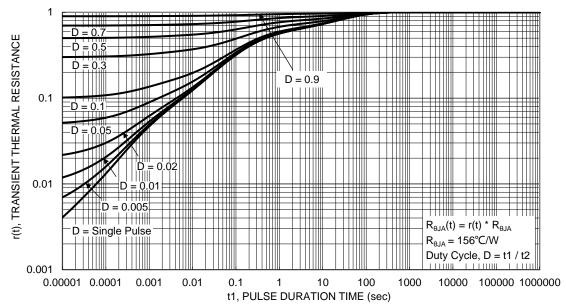


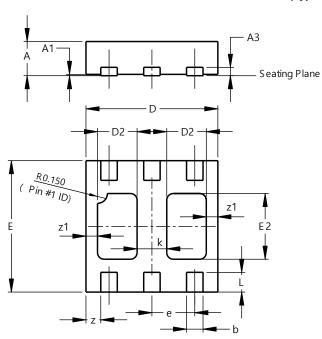
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

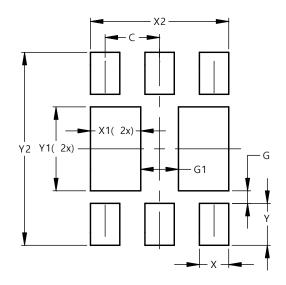


| U-DFN2020-6 Type B | | | | | | |
|-----------------------|--------|---------|-------|--|--|--|
| Dim | Min | Max | Тур | | | |
| Α | 0.545 | 0.605 | 0.575 | | | |
| A1 | 0.00 | 0.05 | 0.02 | | | |
| A3 | - | - | 0.13 | | | |
| b | 0.20 | 0.30 | 0.25 | | | |
| D | 1.95 | 2.075 | 2.00 | | | |
| D2 | 0.50 | 0.70 | 0.60 | | | |
| е | - | - | 0.65 | | | |
| Е | 1.95 | 2.075 | 2.00 | | | |
| E2 | 0.90 | 1.10 | 1.00 | | | |
| k | - | - | 0.45 | | | |
| L | 0.25 | 0.35 | 0.30 | | | |
| Z | - | - | 0.225 | | | |
| z1 | - | - | 0.175 | | | |
| All | Dimens | ions in | mm | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



| Dimensions | Value |
|------------|---------|
| 2 | (in mm) |
| C | 0.650 |
| G | 0.150 |
| G1 | 0.450 |
| Х | 0.350 |
| X1 | 0.600 |
| X2 | 1.650 |
| Y | 0.500 |
| Y1 | 1.000 |
| Y2 | 2.300 |



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